

Transient Voltage Suppressors

ESD Protection Diodes with Ultra-Low Capacitance

The ESD8LF is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Specification Features:

- Ultra Low Capacitance 0.4 pF
- Low Clamping Voltage
- Small Body Outline Dimensions: 1.00 mm x 0.60 mm
- Low Body Height: 0.5 mmStand-off Voltage: 5.5 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000-4-2 Level 4 ESD Protection
- This is a Pb-Free Device

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic

Epoxy Meets UL 94 V-0

LEAD FINISH: 100% Matte Sn (Tin)

QUALIFIED MAX REFLOW TEMPERATURE: $260^{\circ}\mathrm{C}$

Device Meets MSL 1 Requirements

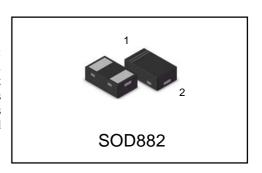
MAXIMUM RATINGS

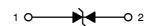
Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact		±10	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C	P _D	150	mW
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature Range	TJ	-55 to +125	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

LESD8LF5.5CT5G





Ordering information

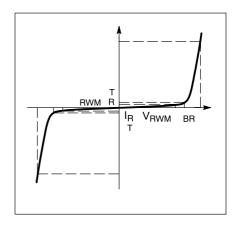
Device	Marking	Shipping	
LESD8LF5.5CT5G	K5	10000/Tape&Reel	



ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

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Symbol	Parameter		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ IPP		
V _{RWM}	Working Peak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V_{BR}	Breakdown Voltage @ I _T		
I _T	I _T Test Current		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		
P _{pk}	Peak Power Dissipation		
С	Capacitance @ V _R = 0 and f = 1.0 MHz		



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		V _{RWM} (V)	I _R (μΑ) @ V _{RWM}		/) @ I _T te 2)	Ι _Τ	C (pF)	V _C (V) @ I _{PP} = 1 A (Note 3)	v _c
Device	Device Marking	Max	Max	Min	Max	mA	Max	Max	Per IEC61000-4-2 (Note 4)
LESD8LF5.5CT5G	K5	5.5	1.0	6.5	11	1.0	0.55	11	Figures 1 and 2 See Below

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.
 Surge current waveform per Figure 4.
 For test procedure see Figures 3.

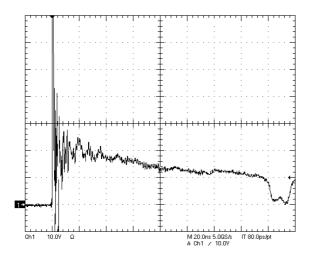


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

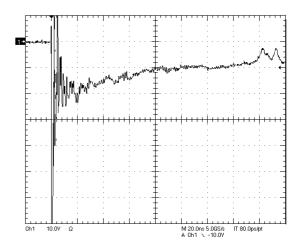


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2



IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

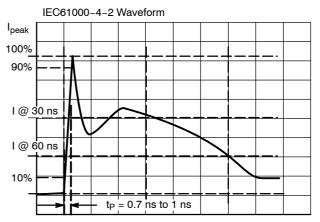


Figure 3. IEC61000-4-2 Spec

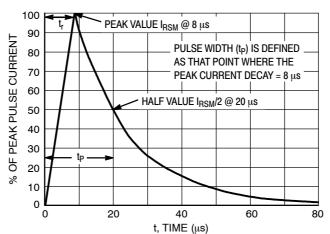
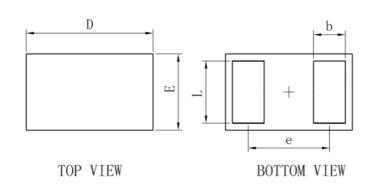


Figure 4. 8 X 20 µs Pulse Waveform

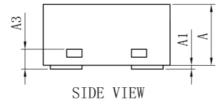


OUTLINE AND DIMENSIONS

SOD882

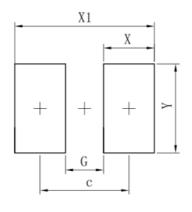


S0D882				
Dim	Min	Min Typ		
D	0.95	1.00	1.05	
Е	0.55	0.60	0.65	
е	-	0.64	-	
L	0.44	0.49	0.54	
b	0.20	0.25	0.30	
A	0.43	0.48	0.53	
A1	0	-	0.05	
A3	3 0. 127REF.			
All Dimensions in mm				



SOLDERING FOOTPRINT

SOD882



Dimensions	(mm)
С	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70